

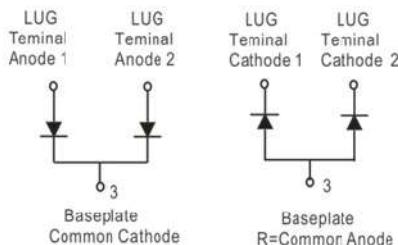
Low V_F Silicon Power Schottky Diode

V_{RRM} =

I_{F(AV)} =

Features

- High Surge Capability
- Type 45 V V_{RRM}
- Not ESD Sensitive

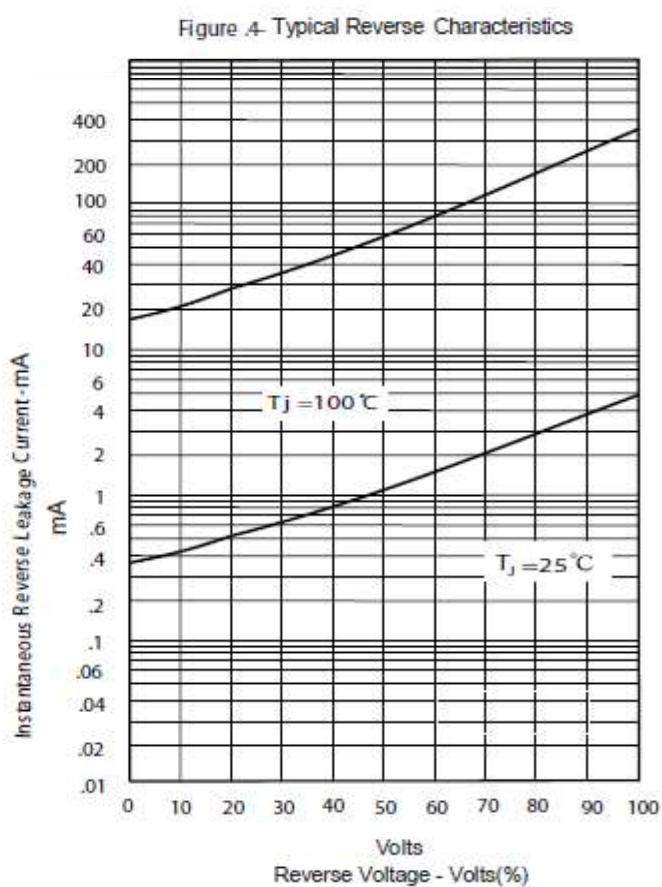
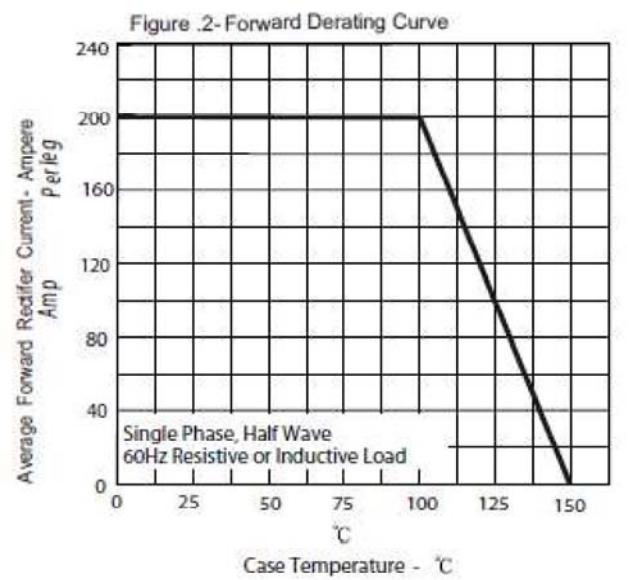
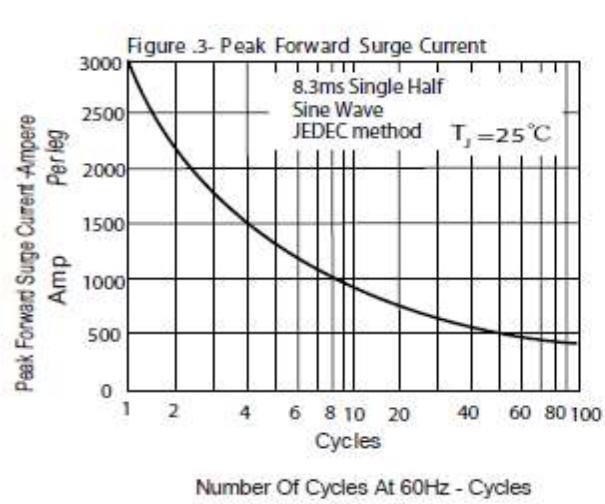
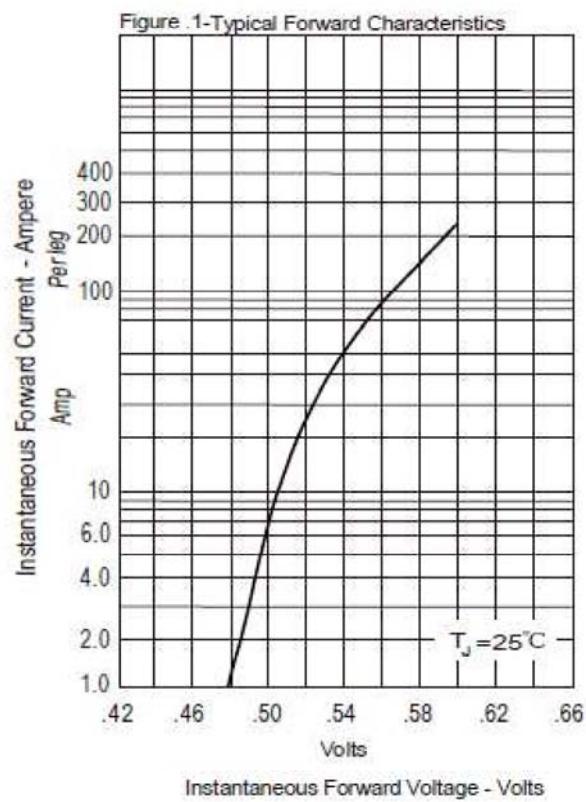
Twin Tower Package


Maximum ratings, at T_j = 25 °C, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR40045CT(R)L	Unit
Maximum recurrent peak reverse voltage	V _{RRM}		45	V
Maximum RMS voltage	V _{RMS}		32	V
Maximum DC blocking voltage	V _{DC}		45	V
Operating temperature	T _j		-55 to 150	°C
Storage temperature	T _{stg}		-55 to 150	°C

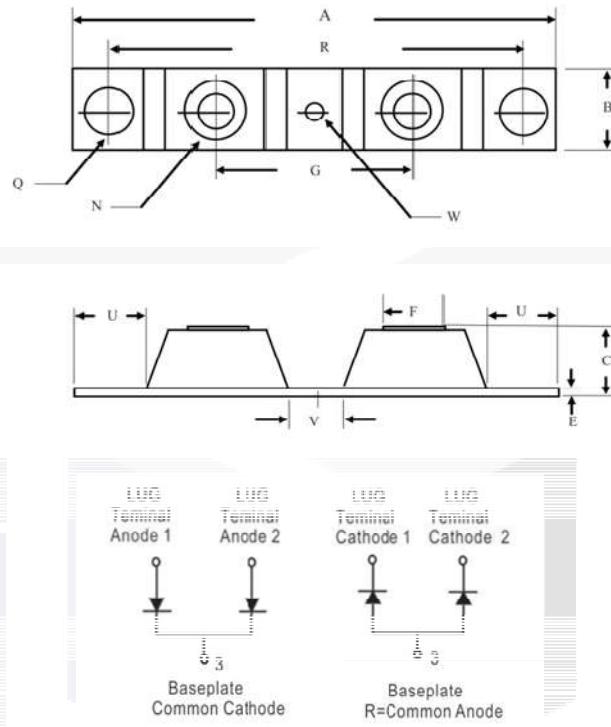
Electrical characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	MBR40045CT(R)L	Unit
Average forward current (per pkg)	I _{F(AV)}	T _C = 100 °C	400	A
Peak forward surge current (per leg)	I _{FSM}	t _p = 8.3 ms, half sine	3000	A
Maximum instantaneous forward voltage (per leg)	V _F	I _{FM} = 200 A, T _j = 25 °C	0.60	V
Maximum instantaneous reverse current at rated DC blocking voltage (per leg)	I _R	T _j = 25 °C T _j = 100 °C	5 350	mA
Thermal characteristics				
Maximum thermal resistance, junction - case (per leg)	R _{θJC}		0.35	°C/W



Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	----	3.630	----	92.40
B	0.700	0.800	17.78	20.32
C	----	0.650	----	16.51
E	0.130	0.141	3.30	3.60
F	0.482	0.490	12.25	12.45
G	1.368	BSC	34.75	BSC
N	1/4-20 UNC FULL			
Q	0.275	0.290	6.99	7.37
R	3.150	BSC	80.01	BSC
U	0.600	----	15.24	----
V	0.312	0.370	7.92	9.40
W	0.180	0.195	4.57	4.95